

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination NAKATA ET AL.	
		Examiner Hai Vo	Art Unit 1771	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,786,498	09-2004	Chang, Owen	280/275
	B	US-4,778,722	10-1988	Yamamura et al.	428/367
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Translation of JP 2001-127152, Nakada et al, "Method for forming low dielectric constant insulation film, low dielectric constant insulation film formed by the same method, and semiconductor device using the low dielectric constant insulation film," May 11, 2001.
	V	English Abstract of JP 64-009231, Niwa et al, "Production of Siloxane Polymer For Forming Insulation Film," January 12, 1989.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.